

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	110mΩ@10V	3A
	160mΩ@4.5V	



合肥矽普半导体

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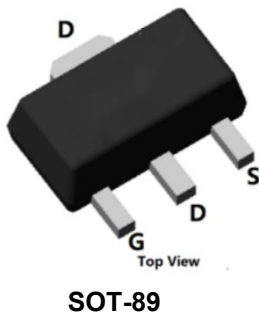
Feature

- High power and current handing capability
- Surface mount package

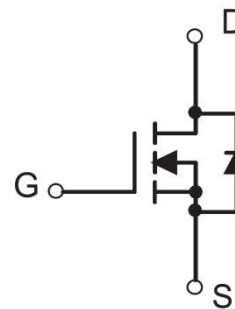
Application

- Battery Switch
- DC/DC Converter

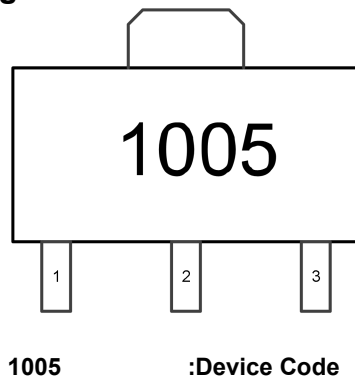
Package



Circuit diagram



Marking



Order Information

Device	Package	Unit/Tape
SP010N110GT8	SOT-89	1000

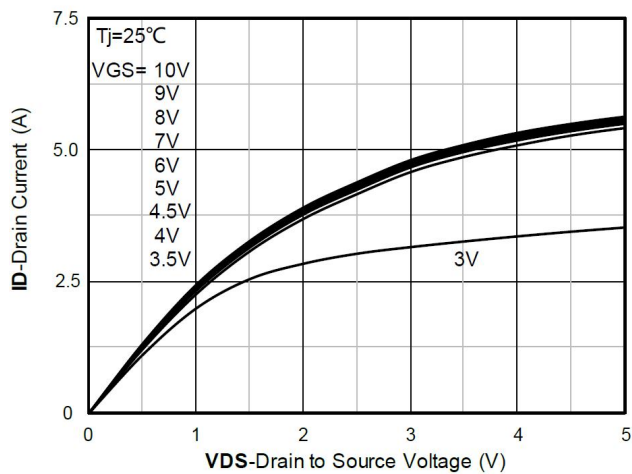
Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	3	A
Pulse Drain Current Tested	I_{DM}	12	A
Power Dissipation	P_D	2.6	W
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	48	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

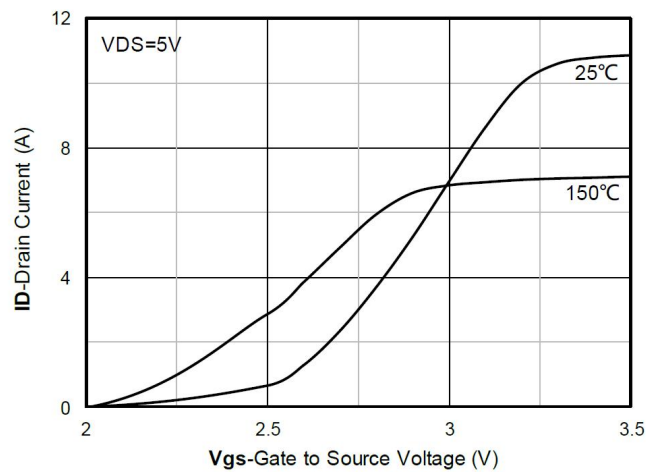
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250μA	100	-	-	V
Drain-Source Leakage Current	IDSS	VDS=60V , VGS=0V	-	-	1	uA
Gate-Source Leakage Current	IGSS	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VDS=VGS , ID=250μA	1.0	1.8	2.5	V
Static Drain-Source On-Resistance	RDS(ON)	VGS =10V, ID =3A	-	110	140	mΩ
		VGS =4.5V, ID =2A	-	160	300	
Dynamic characteristics						
Input Capacitance	Ciss	VDS=50V , VGS=0V , f=1MHz	-	206	-	pF
Output Capacitance	Coss		-	29	-	
Reverse Transfer Capacitance	Crss		-	1.4	-	
Total Gate Charge	Qg	VDS=50V , VGS=10V , ID=3A	-	4.3	-	nC
Gate-Source Charge	Qgs		-	1.5	-	
Gate-Drain Charge	Qgd		-	1.1	-	
Switching Characteristics						
Turn-On Delay Time	td(on)	VDD=50V VGS=10V , RG=2Ω, ID=3A	-	14.7	-	nS
Turn-On Rise Time	tr		-	3.5	-	
Turn-Off Delay Time	td(off)		-	20.9	-	
Turn-Off Fall Time	tf		-	2.7	-	
Source-Drain Diode characteristics						
Diode Forward Voltage	VSD	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V

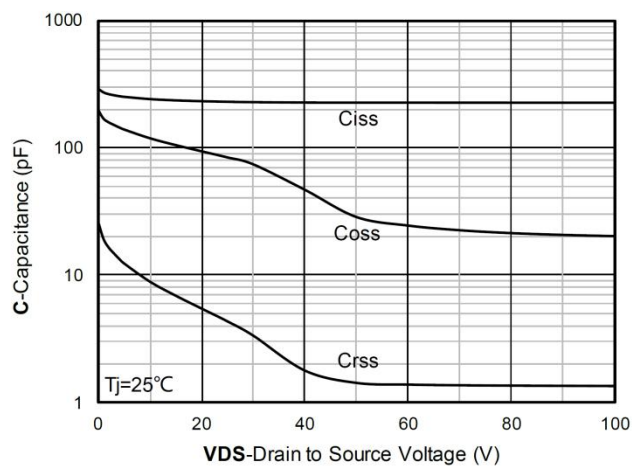
Typical Characteristics



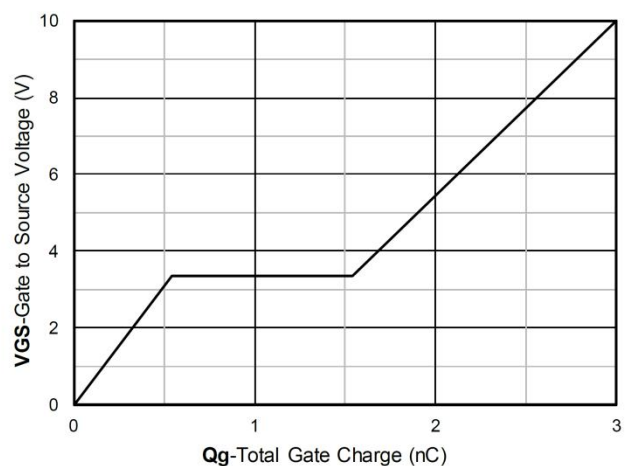
Output Characteristics



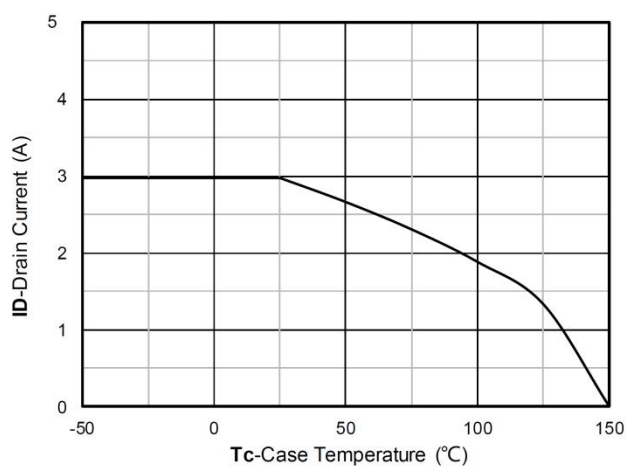
Transfer Characteristics



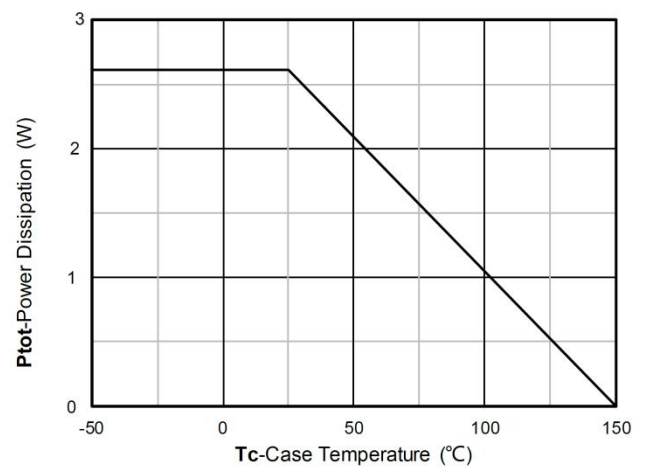
Capacitance Characteristics



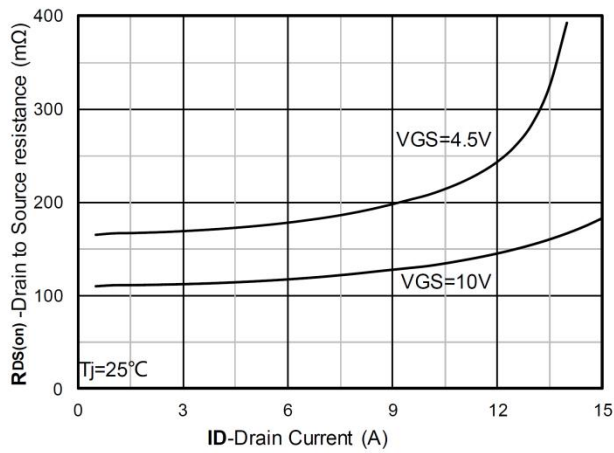
Gate Charge



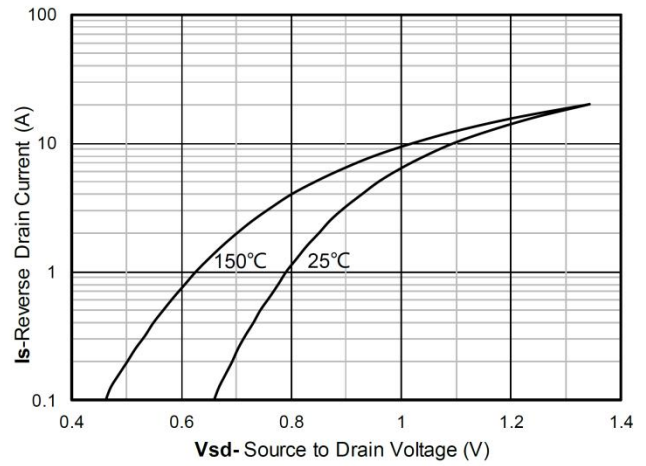
Current dissipation



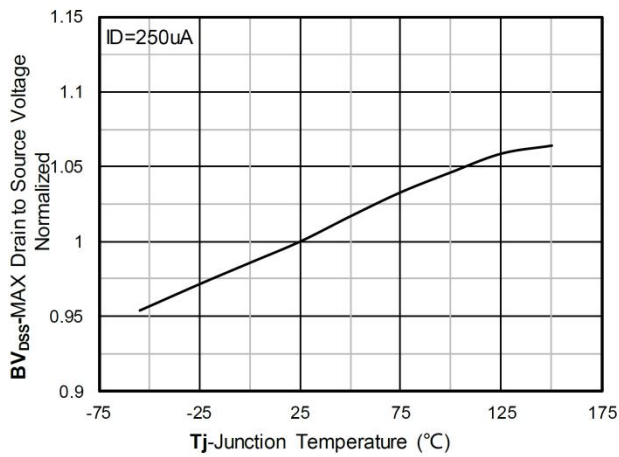
Power dissipation



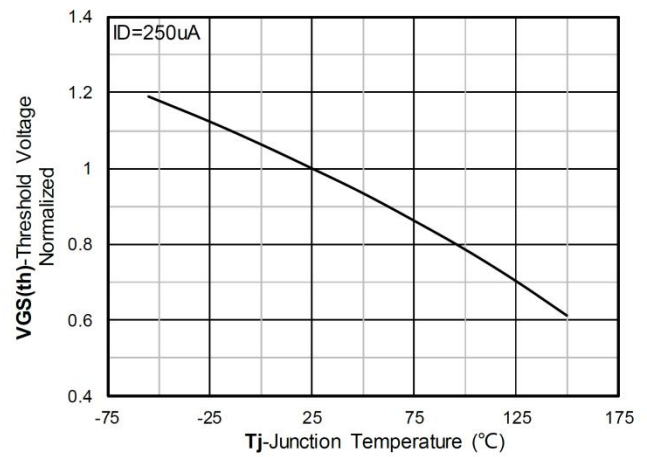
RDS(on) VS Drain Current



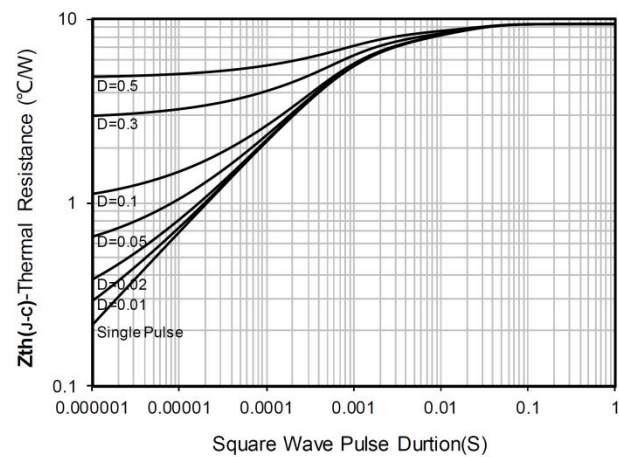
Forward characteristics of reverse diode



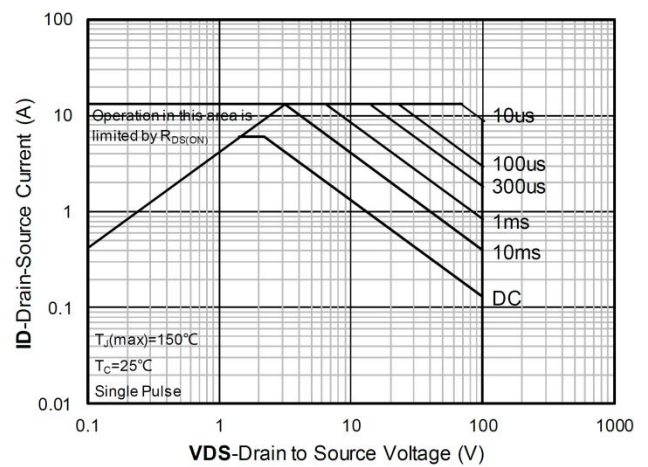
Normalized breakdown voltage



Normalized Threshold voltage

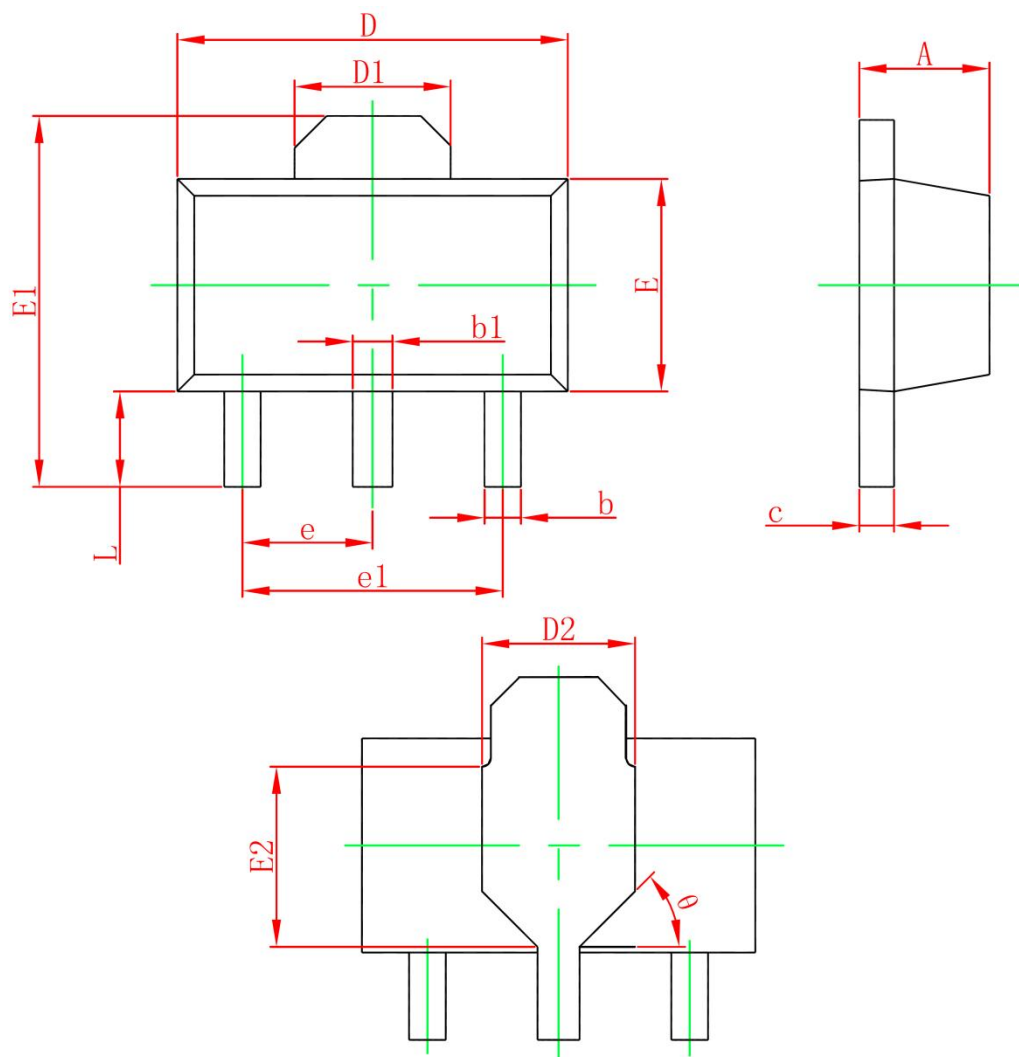


Maximum Transient Thermal Impedance



Safe Operation Area

SOT-89 Package Outline



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	1.400	1.600
b	0.320	0.520
b1	0.400	0.580
c	0.350	0.440
D	4.400	4.600
D1	1.550 REF.	
D2	1.750 REF.	
E	2.300	2.600
E1	3.940	4.250
E2	1.900 REF.	
e	1.500 TYP.	
e1	3.000 TYP.	
L	0.900	1.200
θ	45°	

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